

Ultrasoft Recovery Rectifier Diode

PRODUCT APPLICATIONS

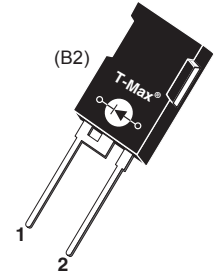
- Anti-Parallel Diode
 - Switchmode Power Supply
 - Inverters
- Applications
 - Induction Heating
- Resonant Mode Circuits
 - ZVS and ZCS Topologies
 - Phase Shifted Bridge

PRODUCT FEATURES

- Ultrasoft Recovery Times (t_{rr})
- Popular TO-247 Package or Surface Mount D³PAK Package
- Ultra Low Forward Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Soft Switching - High Q_{rr}
- Low Noise Switching
 - Reduced Ringing
- Higher Reliability Systems
- Minimizes or eliminates snubber



1 - Cathode
 2 - Anode
 Back of Case - Cathode

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	Ratings	Unit
V_R	Maximum D.C. Reverse Voltage	600	Volts
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		
V_{RWM}	Maximum Working Peak Reverse Voltage		
$I_{F(AV)}$	Maximum Average Forward current ^① ($T_C = 112^\circ\text{C}$, Duty Cycle = 0.5)	150	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	450	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3 ms)	600	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 175	$^\circ\text{C}$
T_L	Lead Temperature for 10 Seconds	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	Min	Typ	Max	Unit	
V_F	Forward Voltage		$I_F = 150\text{A}$	1.25	1.6	Volts
			$I_F = 300\text{A}$	2.0		
			$I_F = 150\text{A}, T_J = 125^\circ\text{C}$	1.25		
I_{RM}	Maximum Reverse Leakage Current		$V_R = 600\text{V}$		25	μA
			$V_R = 600\text{V}, T_J = 125^\circ\text{C}$		250	
C_T	Junction Capacitance, $V_R = 200\text{V}$		139		pF	

DYNAMIC CHARACTERISTICS

APT150DL60B2(G)

Symbol	Characteristic / Test Conditions	Min	Typ	Max	Unit
t_{rr}	Reverse Recovery Time $I_F = 1A, di_F/dt = -100A/\mu s, V_R = 30V, T_J = 25^\circ C$		51		ns
t_{rr}	Reverse Recovery Time		408		
Q_{rr}	Reverse Recovery Charge	$I_F = 150A, di_F/dt = -200A/\mu s, V_R = 400V, T_C = 25^\circ C$	2387		nC
I_{RRM}	Maximum Reverse Recovery Current		13		Amps
t_{rr}	Reverse Recovery Time			639	
Q_{rr}	Reverse Recovery Charge	$I_F = 150A, di_F/dt = -200A/\mu s, V_R = 400V, T_C = 125^\circ C$	7253		nC
I_{RRM}	Maximum Reverse Recovery Current		21		Amps
t_{rr}	Reverse Recovery Time			299	
Q_{rr}	Reverse Recovery Charge	$I_F = 150A, di_F/dt = -1000A/\mu s, V_R = 400V, T_C = 125^\circ C$	12075		nC
I_{RRM}	Maximum Reverse Recovery Current		68		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			0.26	$^\circ C/W$
W_T	Package Weight		0.22		oz
			5.9		g
Torque	Maximum Mounting Torque			10	lb-in
				1.1	N-m

① Continuous current limited by package lead temperature.

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

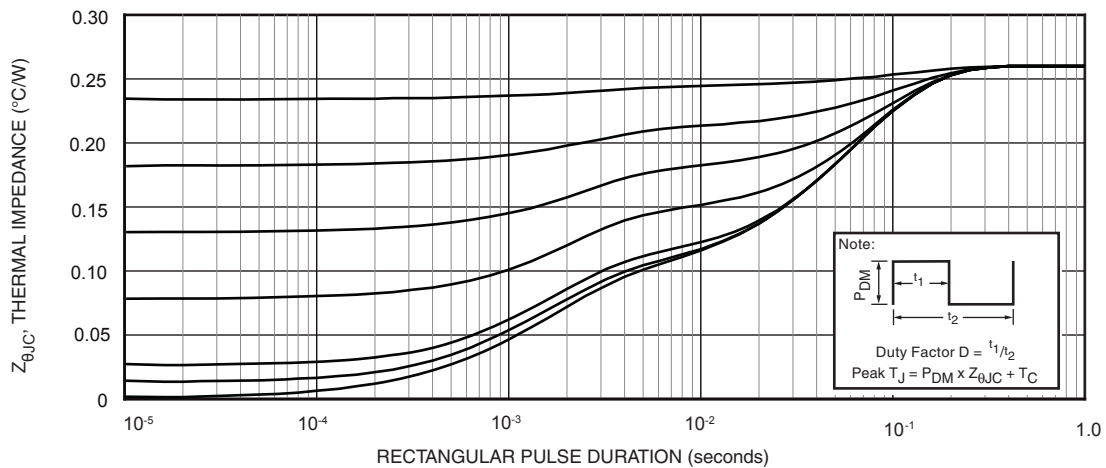


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

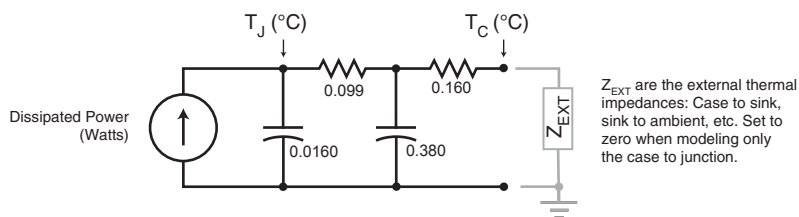


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

TYPICAL PERFORMANCE CURVES

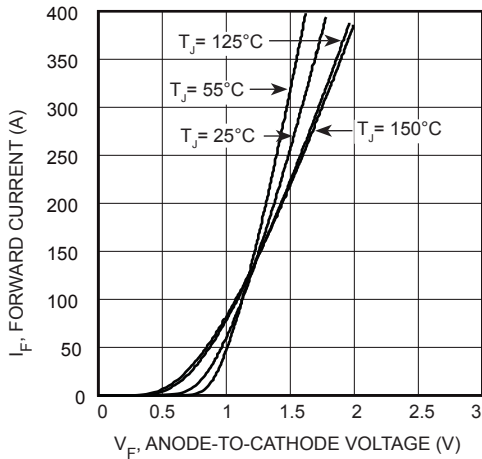


FIGURE 2, Forward Current vs. Forward Voltage

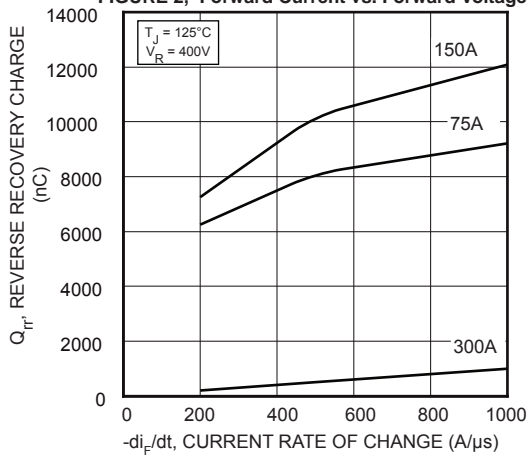


FIGURE 4, Reverse Recovery Charge vs. Current Rate of Change

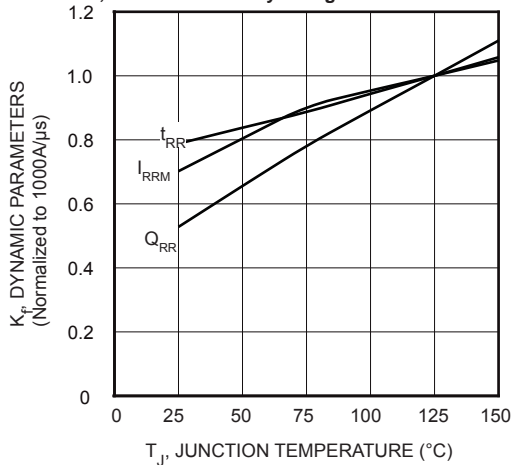


FIGURE 6, Dynamic Parameters vs. Junction Temperature

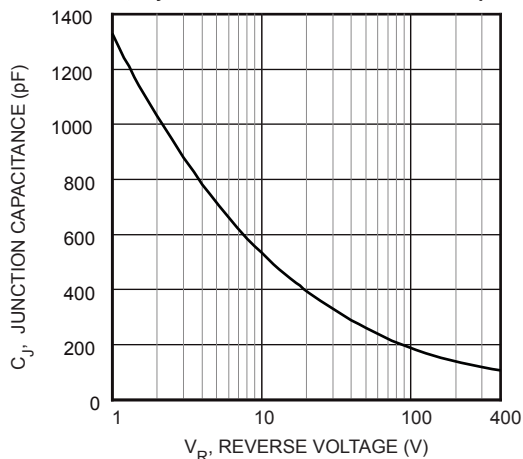


FIGURE 8, Junction Capacitance vs. Reverse Voltage

APT150DL60B2(G)

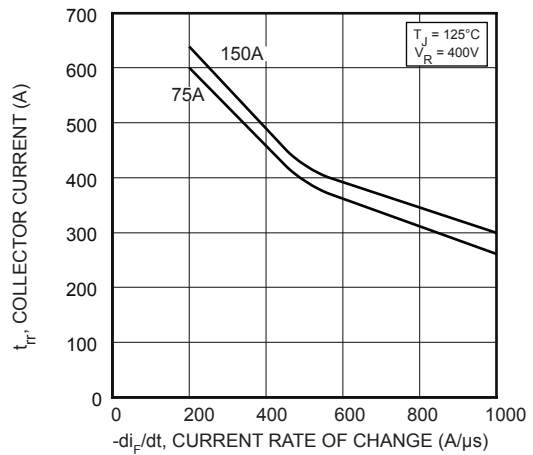


FIGURE 3, Reverse Recovery Time vs. Current Rate of Change

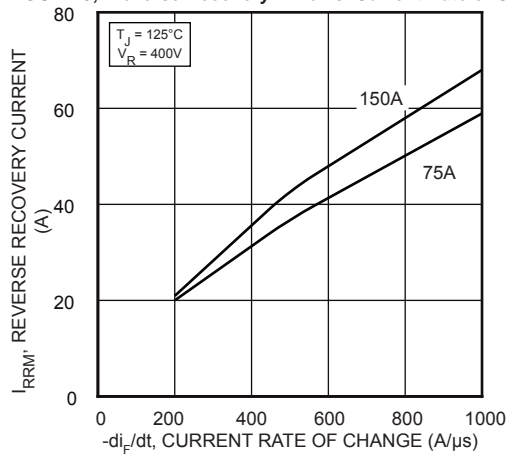


FIGURE 5, Reverse Recovery Current vs. Current Rate of Change

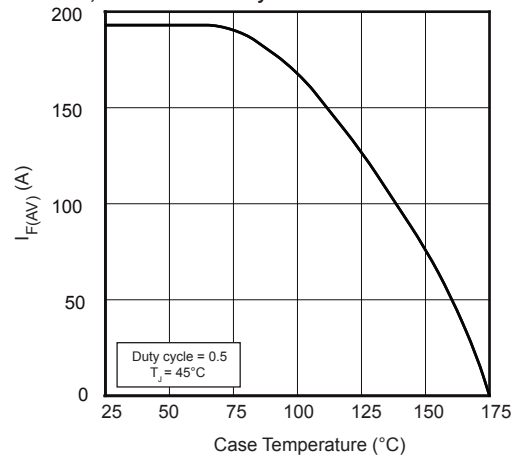


FIGURE 7, Maximum Average Forward Current vs. Case Temperature

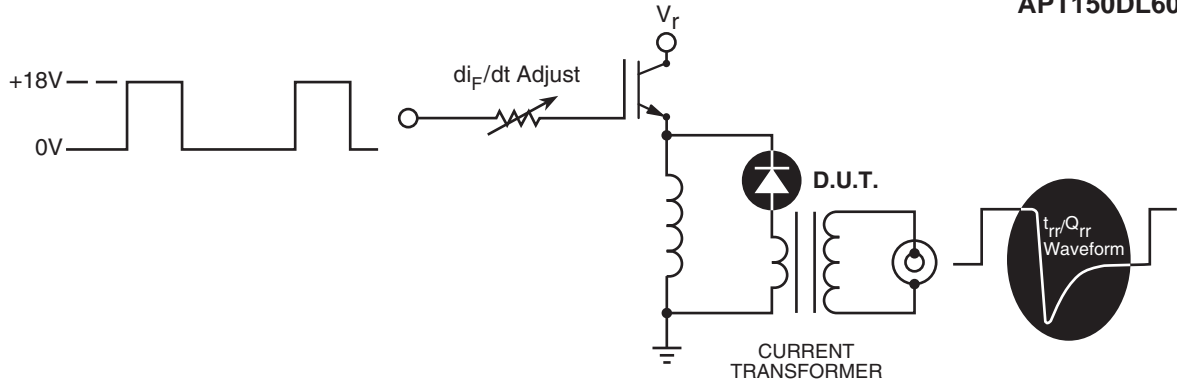


Figure 9. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .
- 6 di_M/dt - Maximum Rate of Current Increase During the Trailing Portion of t_{rr} .

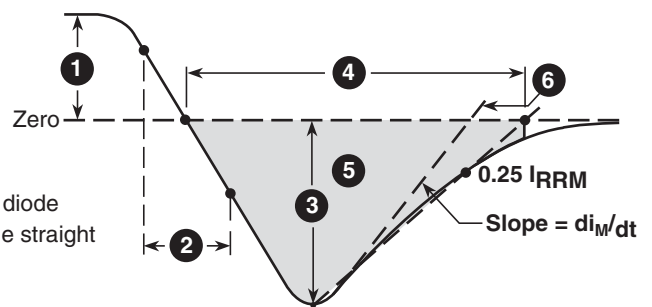
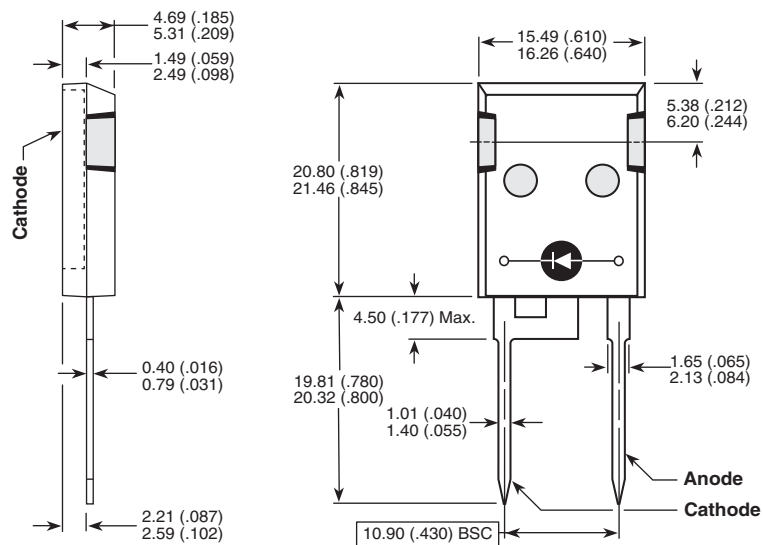


Figure 10, Diode Reverse Recovery Waveform and Definitions

T-MAX® [B2] Package Outline



Dimensions in Millimeters and (Inches)